Photoacoustic spectroscopy of thin films of As$_2$S$_3$, As$_2$Se$_3$ and GeSe$_2$

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MS received 17 February 2006; revised 11 February 2007; accepted 11 April 2007

Abstract. Photoacoustic spectroscopy (PAS) is one of the important branches of spectroscopy, which enables one to detect light-induced heat production following the absorption of pulsed radiation by the sample. As$_2$S$_3$, As$_2$Se$_3$ and GeSe$_2$ exhibit a wide variety of photo-induced phenomena that enable them to be used as optical imaging or storage medium and various electronic devices, including electro-optic information storage devices and optical mass memories. Therefore, accurate measurement of thermal properties of semiconducting films is necessary to study the memory density. The thermal conductivity of thin films of As$_2$S$_3$ (thickness 100 μm and 80 μm), As$_2$Se$_3$ (thickness 100 μm and 80 μm) and GeSe$_2$ (thickness 120 μm and 100 μm) has been measured using PAS technique. Our result shows that the thermal conductivity of thicker films is larger than the thinner films. This can be explained by the thermal resistance effect between the film and the surface of the substrate.

Keywords. Thermal conductivity; thermal resistance; semiconducting thin films.

PACS Nos 43.35.Vz; 43.35.Sx; 43.25.Qp

1. Introduction

The photoacoustic effect [1] is an effective method of determining thermal parameters of various materials when the PA signal is measured as a function of chopping frequency. The suitability of the photoacoustic (PA) technique lies in the fact that it can be applied irrespective of the physical state of the sample, i.e. solid, semisolid, liquid, gel etc. [2,3]. As$_2$S$_3$, As$_2$Se$_3$ and GeSe$_2$ exhibit many properties, including a high refractive index, and excellent transmission at infrared wavelengths. Thus these are very promising glasses for ultrafast all-optical switching. Semiconducting thin films have potential application in optoelectronis. However, the thermal properties were not widely investigated compared to the optical and electrical properties [4,5]. In this work we report that the thermal conductivity of thin films of As$_2$S$_3$, As$_2$Se$_3$ and GeSe$_2$ changes with the thickness of the film.
2. Experimental set-up

Thin films of $\text{As}_2\text{S}_3$, $\text{As}_2\text{Se}_3$ and $\text{GeSe}_2$ were prepared by the thermal deposition of $\text{As}_2\text{S}_3$, $\text{As}_2\text{Se}_3$ and $\text{GeSe}_2$ onto transparent slides under a pressure of $\sim (1-2) \times 10^{-7}$ Torr at a rate of $\sim 3$ nm/s. The measurements are taken at room temperature. The experimental apparatus for PAS measurements is shown in figure 1. A He–Ne laser (wavelength 632.8 nm) is used as a light source. The light beam was modulated by a mechanical chopper (Model Sr 540, Stanford, USA) and directed to the sample compartment of the PA cell through the quartz window. The PA signal produced is processed by using a pre-amplifier and a lock-in amplifier.

3. Results and discussion

The log–log plots of the variation in photoacoustic signal with chopping frequency for $\text{As}_2\text{S}_3$ (thickness 100 $\mu$m and 80 $\mu$m), $\text{As}_2\text{Se}_3$ (thickness 100 $\mu$m and 80 $\mu$m) and $\text{GeSe}_2$ (thickness 120 $\mu$m and 100 $\mu$m) are shown in figure 2. Thermal diffusivity can be evaluated using the relation $\alpha = t_f^2 f_C$, where $t_f$ is the thickness of the examined sample and $f_C$ is the characteristic frequency. The measurement of $\alpha$ allows us to determine thermal conductivity ($\kappa$) by the relation $\kappa = (\rho \propto c)$. Here $\rho$ is the density and $c$ is the specific heat. The specific heat of $\text{As}_2\text{S}_3$, $\text{As}_2\text{Se}_3$ and $\text{GeSe}_2$ are 0.247 $\text{J/kg} \cdot \text{K}$, 0.429 $\text{J/kg} \cdot \text{K}$ and 0.308 $\text{J/kg} \cdot \text{K}$ [6] and the densities of these thin films are 3.46 $\text{g/cm}^3$, 4.75 $\text{g/cm}^3$ and 4.56 $\text{g/cm}^3$ respectively [7]. The values of thermal conductivity are tabulated in table 1.